



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-06C Plastic-Encapsulate Diode

FBAS70DW-05

SURFACE MOUNT SCHOTTKY BARRIER DIODE ARRAYS

DESCRIPTION

Silicon epitaxial planar

PN Junction Guard Ring for Schottky Diode

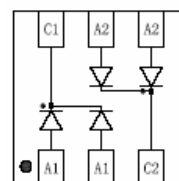
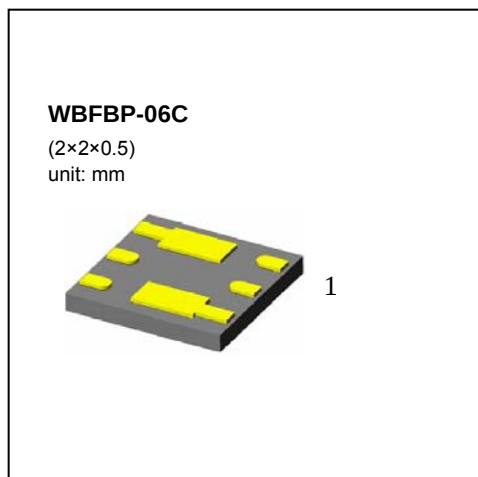
FEATURES

- Low Forward Voltage Drop
- Fast Switching
- Ultra-Small Surface Mount Package

APPLICATION

For General Purpose Switching Applications, rectifiers

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)



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Marking:K71

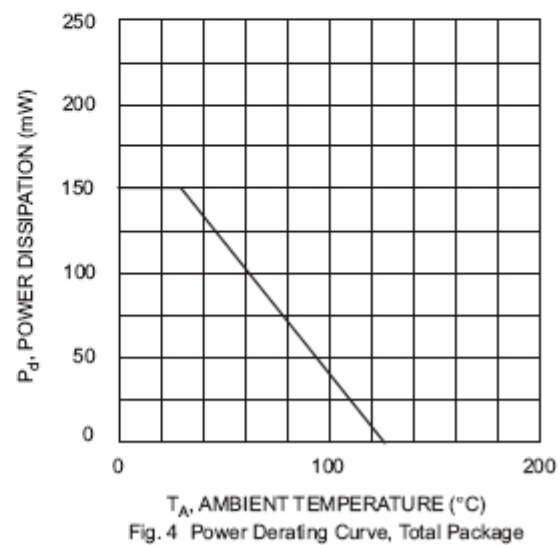
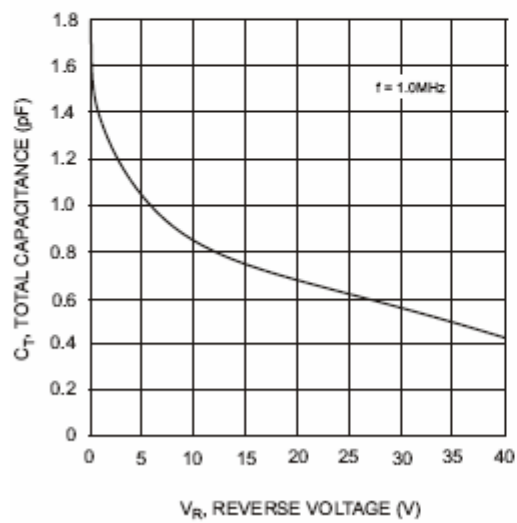
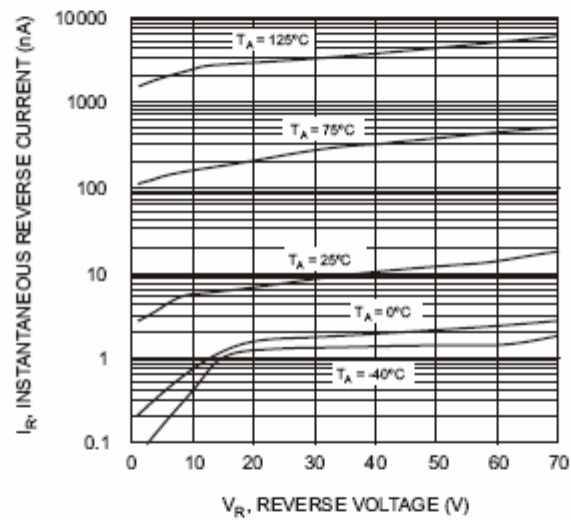
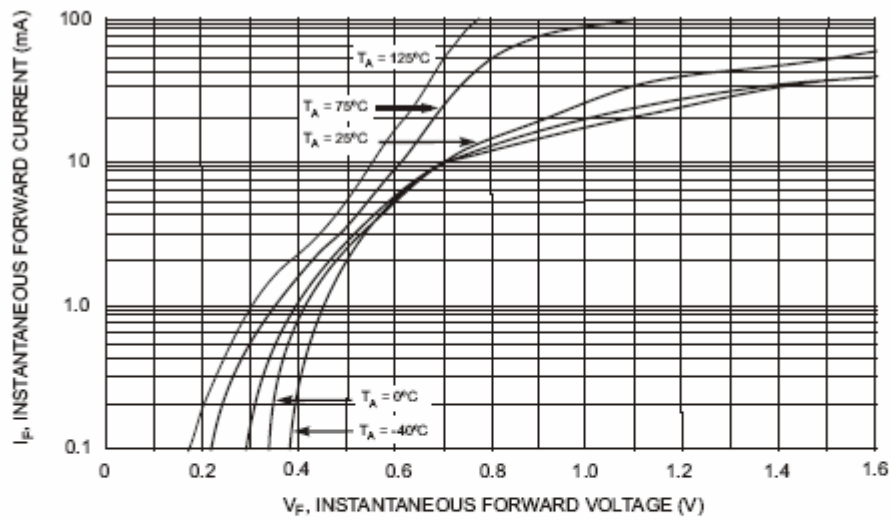
Maximum Ratings @T_A=25

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	70	V
Forward Continuous Current	I _F	70	mA
Peak forward surge current @<1.0s	I _{FSM}	100	mA
Power Dissipation	P _d	150	mW
Thermal Resistance Junction to Ambient	R _{θJA}	625	°C/W
Junction temperature	T _J	125	°C
Storage temperature range	T _{STG}	-55 to +125	°C

Electrical Ratings @T_A=25°C

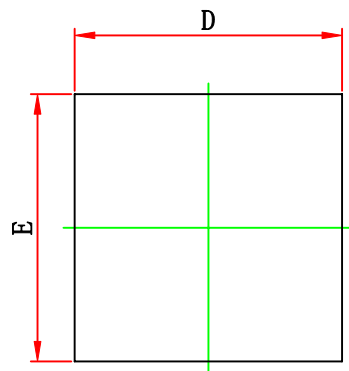
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{F1}			0.41	V	I _F =1mA
	V _{F2}			1	V	I _F =15mA
Reverse current	I _R			100	nA	V _R =50V
Capacitance between terminals	C _T			2	pF	V _R =0V,f=1MHz
Reverse Recovery Time	t _{rr}			5	ns	I _F =I _R =10mA I _{rr} =0.1X I _R , R _L =100Ω

Typical Characteristics

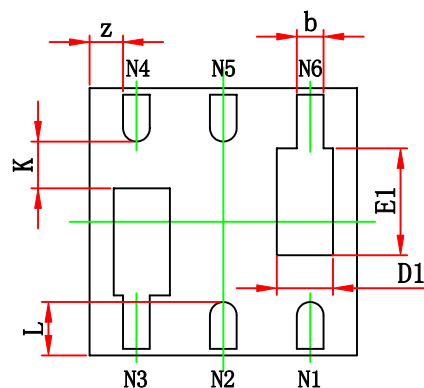




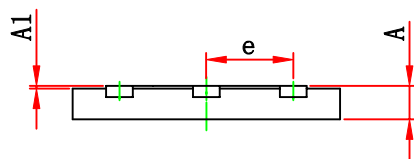
WBFBP-06C(2×2×0.5) PACKAGE OUTLINE DIMENSIONS



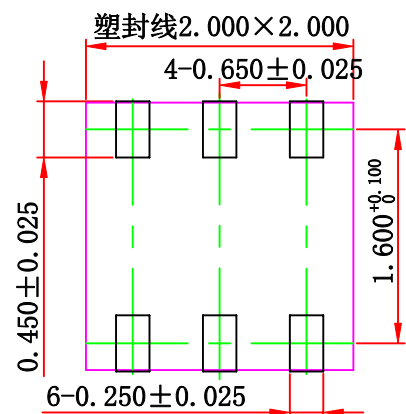
TOP VIEW



BOTTOM VIEW



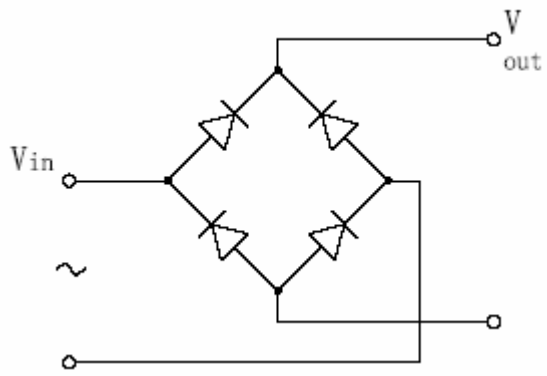
SIDE VIEW



LAND PATTERN RECOMMENDATION
推荐焊盘图

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.000	0.100	0.000	0.004
b	0.150	0.250	0.006	0.010
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	0.420 REF.		0.017 REF.	
E1	0.800 REF.		0.032 REF.	
e	0.650 TYP.		0.026 TYP.	
L	0.400 REF.		0.016 REF.	
k	0.350 REF.		0.014 REF.	
z	0.500 REF.		0.020 REF.	

APPLICATION CIRCUITS



Bridge rectifiers